



# SCAPE 2019

International Wide-BandGap Power Electronics Applications Workshop

12-14 May 2019, Stockholm, Sweden

Workshop Programme

13-14 May

# Workshop SCAPE 2019

13-14 May 2019, Radisson Blu Royal Park Hotell

## Monday 13 May

08:30 - 09:00	Registration & coffee
09:00	Mietek Bakowski, RISE: Welcome
<i>Strategic Initiatives</i>	
09:10	Peter Rechberger, ECPE: ECPE WBG Roadmap - lead applications for SiC and GaN
09:30	Peder Bergman, Linköping University: Presentation of PECTA - speeding-up effectivisation of energy conversion
09:50	Alistair McGibbon, UK Catapult programme: Supporting industrial R&D in wide bandgap power electronics applications
10:10 - 10:50	Coffee & Exhibition
<b>Key Note</b>	
10:50	Enrico Zanoni, University of Padova: Recent advancements in the technology and reliability of power Gallium Nitride devices for switching applications
<i>SiC &amp; GaN Devices</i>	
11:20	John Palmour, Wolfspeed: SiC MOSFETs Poised for Adoption in Automotive Markets
11:40	Ignazio Lizama, ROHM Semiconductor: SiC MOSFETs in Low-Inductive SMD Package with driver Source
12:00	Martin Domeij, On Semiconductor: Rugged 1200 V SiC MOSFETs for automotive applications
12:20 - 14:00	Lunch & Exhibition
14:00	Juan Colmenares, Infineon : Silicon Carbide CoolSiC™ semiconductor products - revolution to rely on
14:20	Eugen Wiesner, Mitsubishi Electric: SiC Power Modules and their applications
<b>Applications</b>	
14:40	Nicola Mingirulli, Robert Bosch: SiC in Automotive Drivetrain Application
15:00 - 15:20	Coffee & Exhibition
15:20	Martin Lindahl, Bombardier Transportation Sweden: Investigation of Overvoltage On Motor Terminal Due to Fast Switching with Silicon Carbide
15:40	Thord Nilson, Inmotion Technologies: Evaluation of performance of WBG (and Si) components for inverter applications
16:00	Kenneth Andersson, QRTECH: 5kW PFC Vienna rectifier for Airborne Equipment
16:20 - 16:40	Coffee & Exhibition
16:40	Stefan Lidström, Comsys: WBG components is not the "simple solution" - a good system design is equally important
17:00	Christian Schwabe, Chemnitz University of Technology: Power cycling of SiC Mosfets
17:20	Ninos Poli, Scania: Voltage Source Converter using SiC for Scania's electrified vehicles
<i>WBG PC Annual Awards</i>	
17:40	Presentation of awardees "Best Master Thesis" & "Young Professional" Per Ranstad, WBG Power Center
17:50 - 18:10	Best Master Thesis & Young Professional Award, summary given by awardees
19:30	Dinner

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## Tuesday 14 May

08:30 - 09:00 Registration & coffee

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### GaN Devices & Modules

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09:00 **Thierry Bouchet, Leti**  
*A new 650V GaN Half Bridge Power IC to Reach Ultimate USB Power Delivery Efficiency*

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09:20 **Marco Panizza, Panasonic**  
*Hybrid Drain GIT GaN based Totem Pole PFC Design - Reliability and circuital considerations*

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09:40 **Mattia Guacci, ETH**  
*Analysis of Monolithic Bidirectional GaN-switches and a New Modulation Scheme for Three-phase CSIs*

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10:00 - 10:30 Coffee & Exhibition

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### Resonant Convertors

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10:30 **Enrique Dede, Smart Induction Converter Technologies**  
*SiC Ultra Compact Smart Inverter Module for Induction Heating Applications*

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10:50 **John Kåre Langelid, EFD Induction**  
*Practical Experiences Using SiC DioMos in High Frequency High Power Series Resonant Applications*

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11:10 **Per Ranstad, KTH, Royal Institute of Technology**  
*On switching losses in a soft switching resonant converter*

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### SiC MOSFET Analysis

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11:30 **Andreas Huerner, Infineon: Compact-Models for SiC-MOSFETs**

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11:50 **Amine Allouche, System Plus Consulting: SiC Power MOSFETs State of the Art - Technology and Cost Overview**

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12:10 - 13:30 Lunch & Exhibition

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### Market & Roadmap

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13:30 **Hong Lin, Yole Développement: GaN & SiC power devices - Market overview**

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14:00 **Edoardo Merli, STMicroelectronics: SiC applications, growth and manufacturing strategy**

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### Panel Discussion

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14:20 **Chair: Hong Lin, Yole Développement**  
*Do we move towards wafer manufacturing integration & Can SiC production survive the automotive growth / boom*  
**Panelists:** John Palmour, Edoardo Merli, P.S. Raghavan, Martin Domeij

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15:00 **Volker Sinhoff, KCEO AIXaTECH: Low Temperature Epitaxy (LTE) - a corner stone for price parity between silicon and wide bandgap semiconductors**

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### Packaging

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15:20 **Kirill Klein, Fraunhofer IZM: The Evolution of Low Inductive Power Modules**

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15:40 **Uffe Pless, UnitedSiC: 5 Design Tips for Easy SiC Implementation**

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### Closing Remarks

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16:00 **Hans-Peter Nee, KTH, Royal Institute of Technology**

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16:20 **End of workshop**

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Ascatron provides next generation Silicon Carbide (SiC) power semiconductors radically reducing losses in power converters. The high voltage power devices are based on Ascatron proprietary 3DSiC® material technology with buried doping structures to reduce the surface electric field. This gives very robust devices with lower losses and reliable operation at full power. Target applications are high voltage power electronics used in industry, automotive and renewable energy.

Ascatron is a Sweden based scale-up company with background in producing advanced SiC epitaxy material for global customers since 2011.



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EK Power Solution has 22 employees with 23 years of average engineering experience in power electronics. We are certified according to ISO9001 and 14001.



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GT Advanced Technologies is a diversified technology company with crystalline growth expertise in silicon, silicon carbide, and sapphire. Our advanced materials deliver sustained value to the worlds top manufacturers in the global photovoltaics, power electronics and opto-electronics markets. Our innovative technologies and industry experience drive the development and commercialization of products that elevate performance, improve quality and lower manufacturing costs.



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